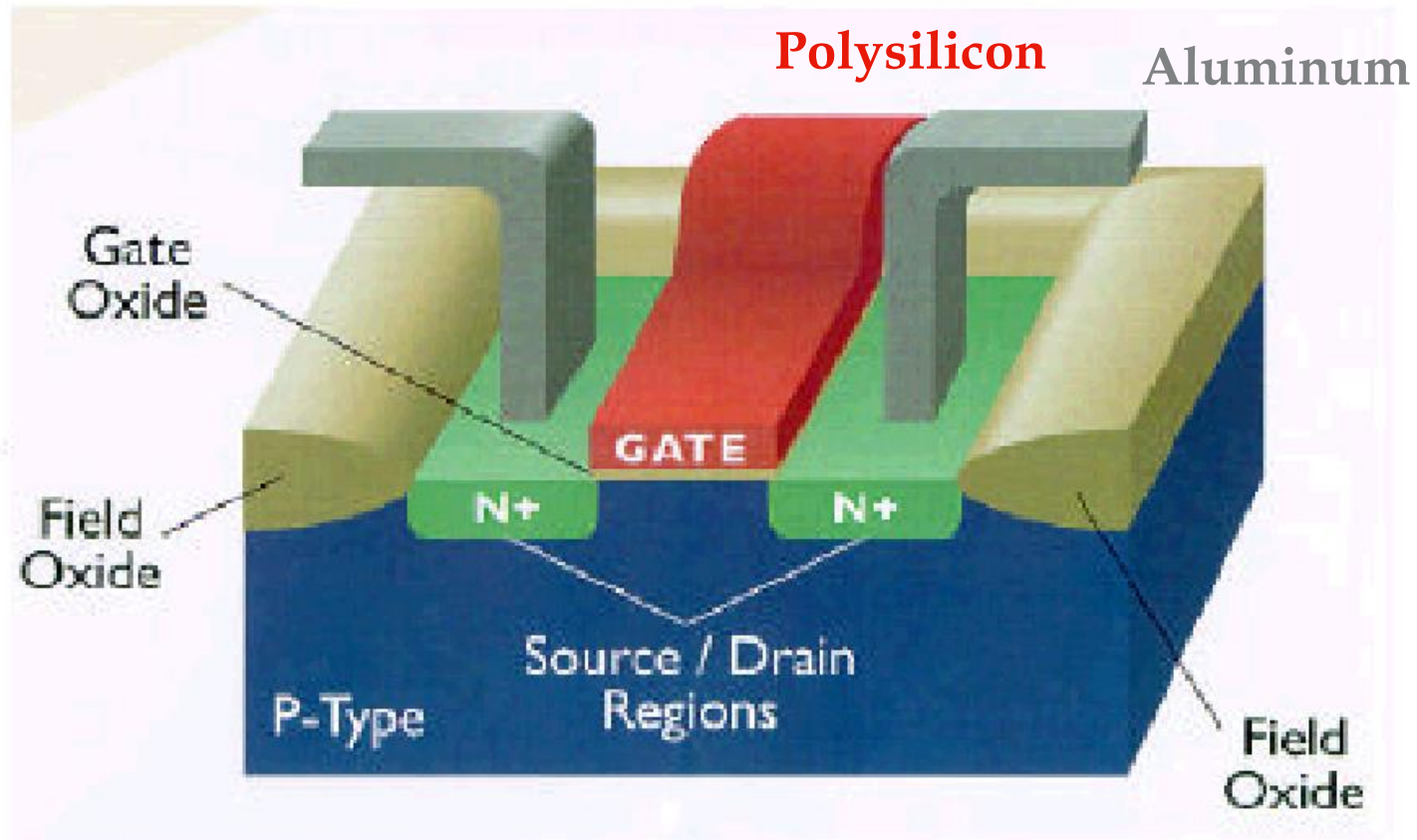


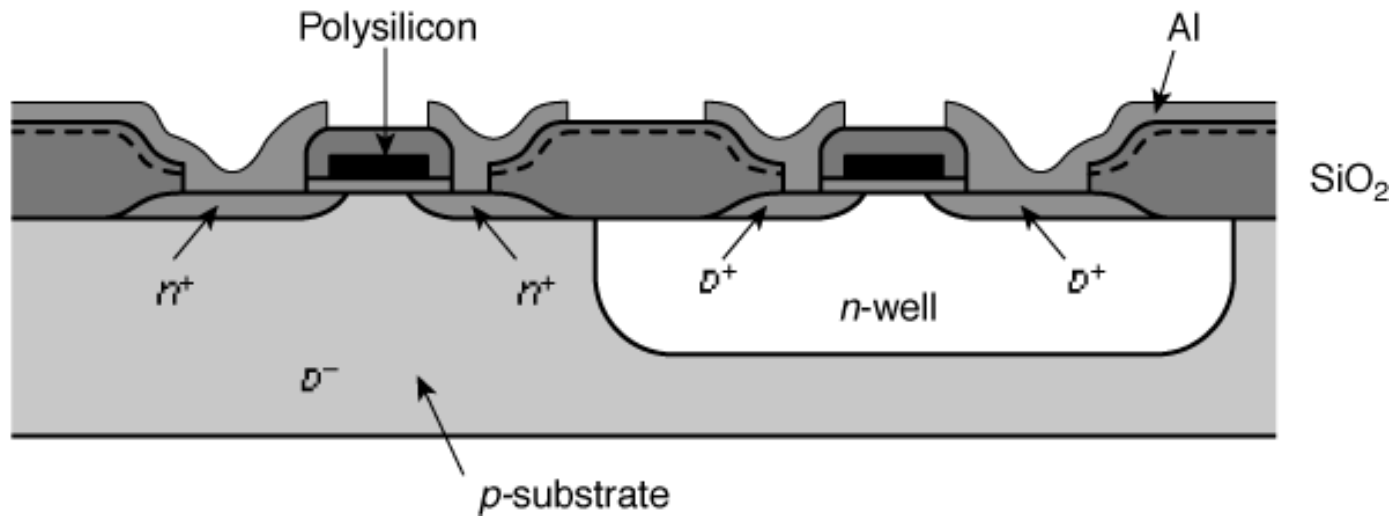
INTRODUCTION TO
FULL-CUSTOM LAYOUT
(Chapter 2)

AND THE *MAGIC* LAYOUT TOOL

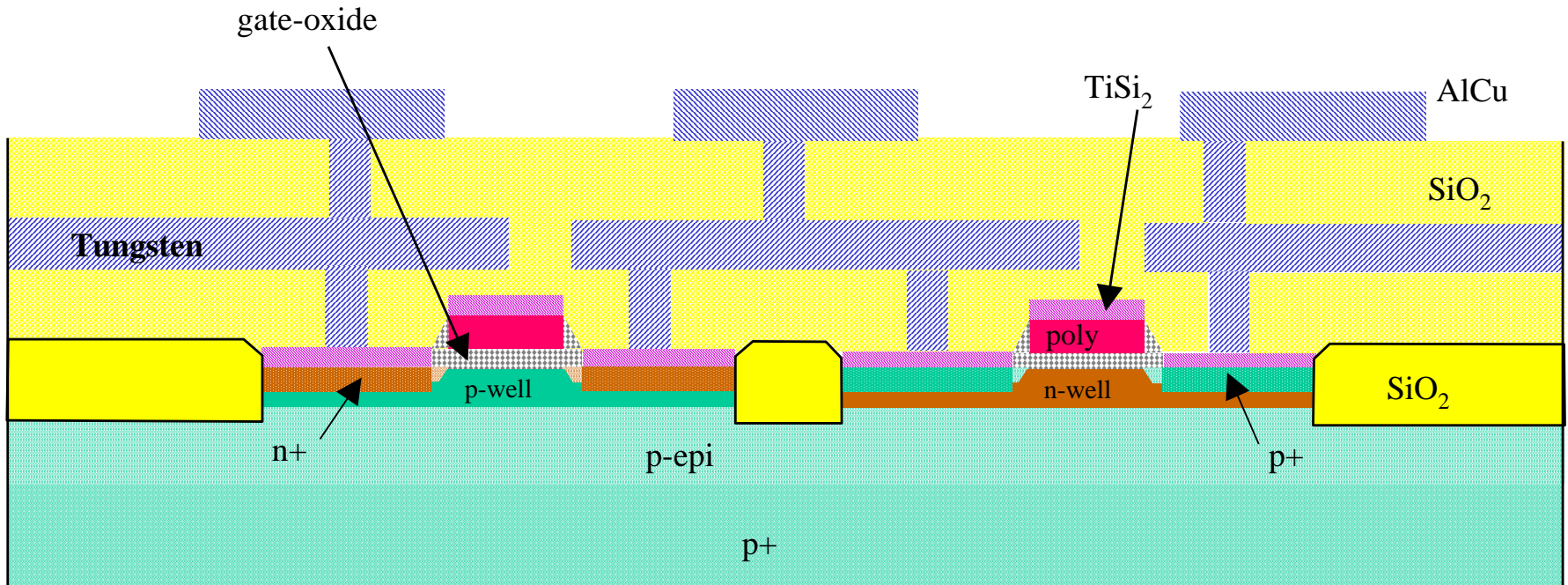
3D Perspective



CMOS Process



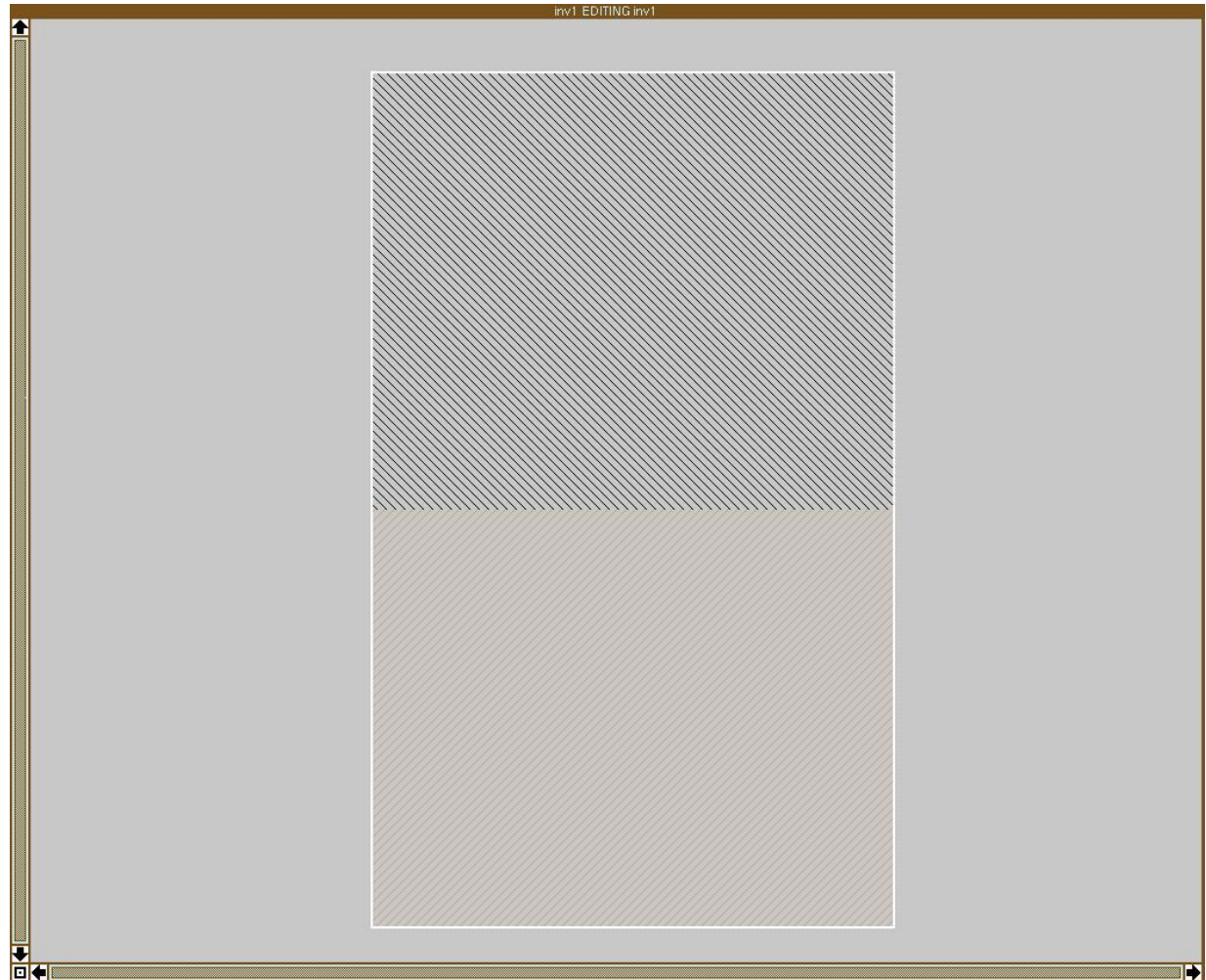
A Modern CMOS Process



Dual-Well Trench-Isolated CMOS Process

nwell and pwell

- The “bodies” of the transistors



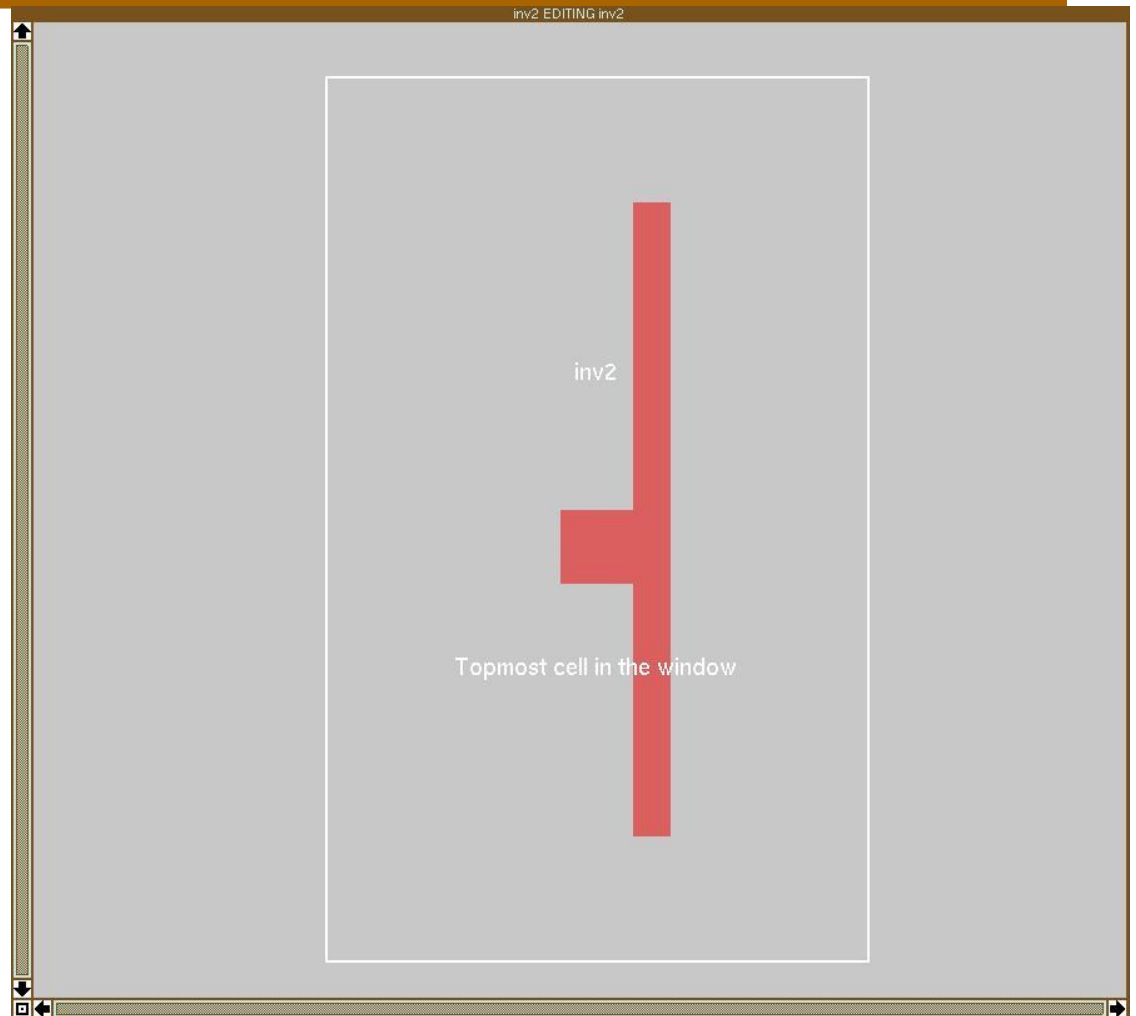
ndiffusion and pdiffusion

- Source and Drain for each transistor



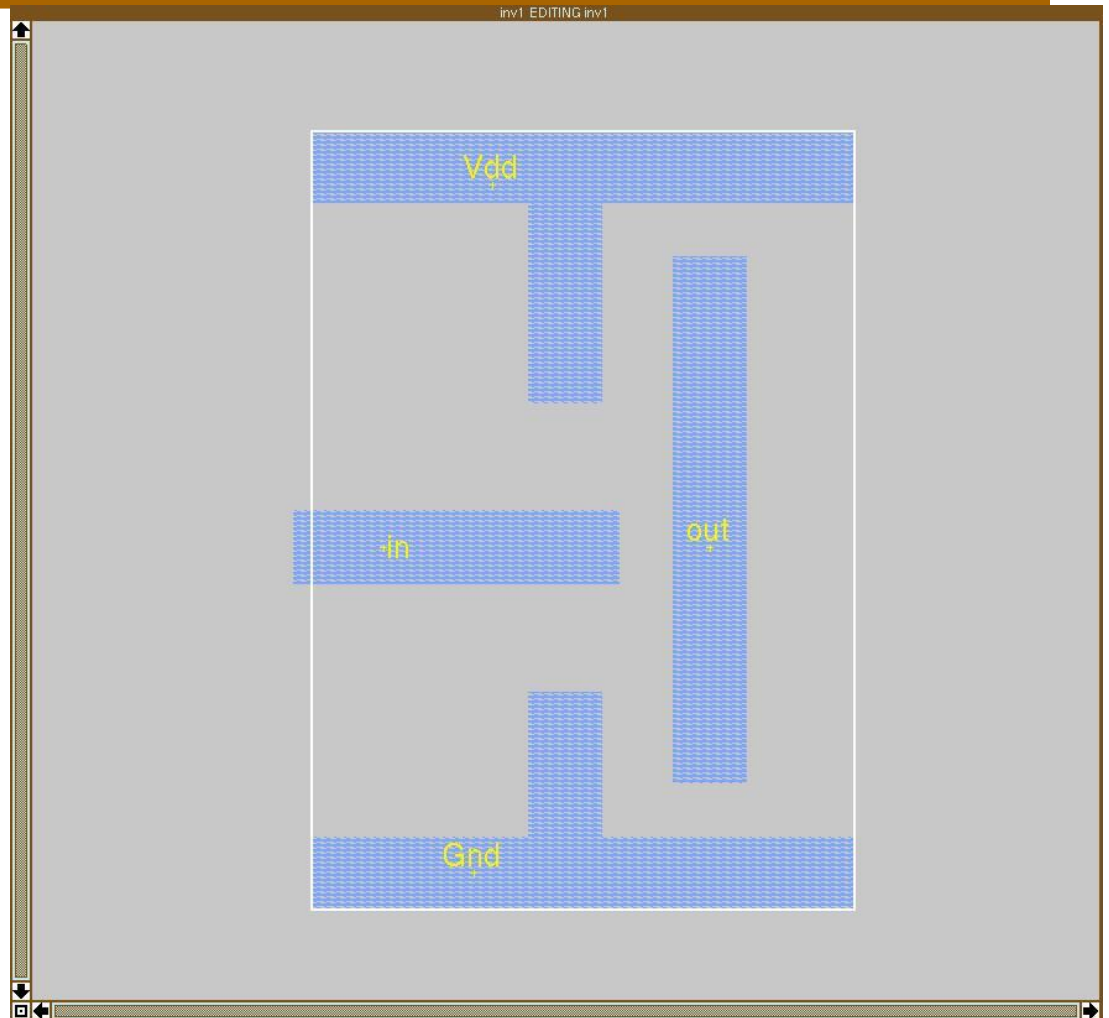
Polysilicon

- Gate of transistors and for short-distance wiring



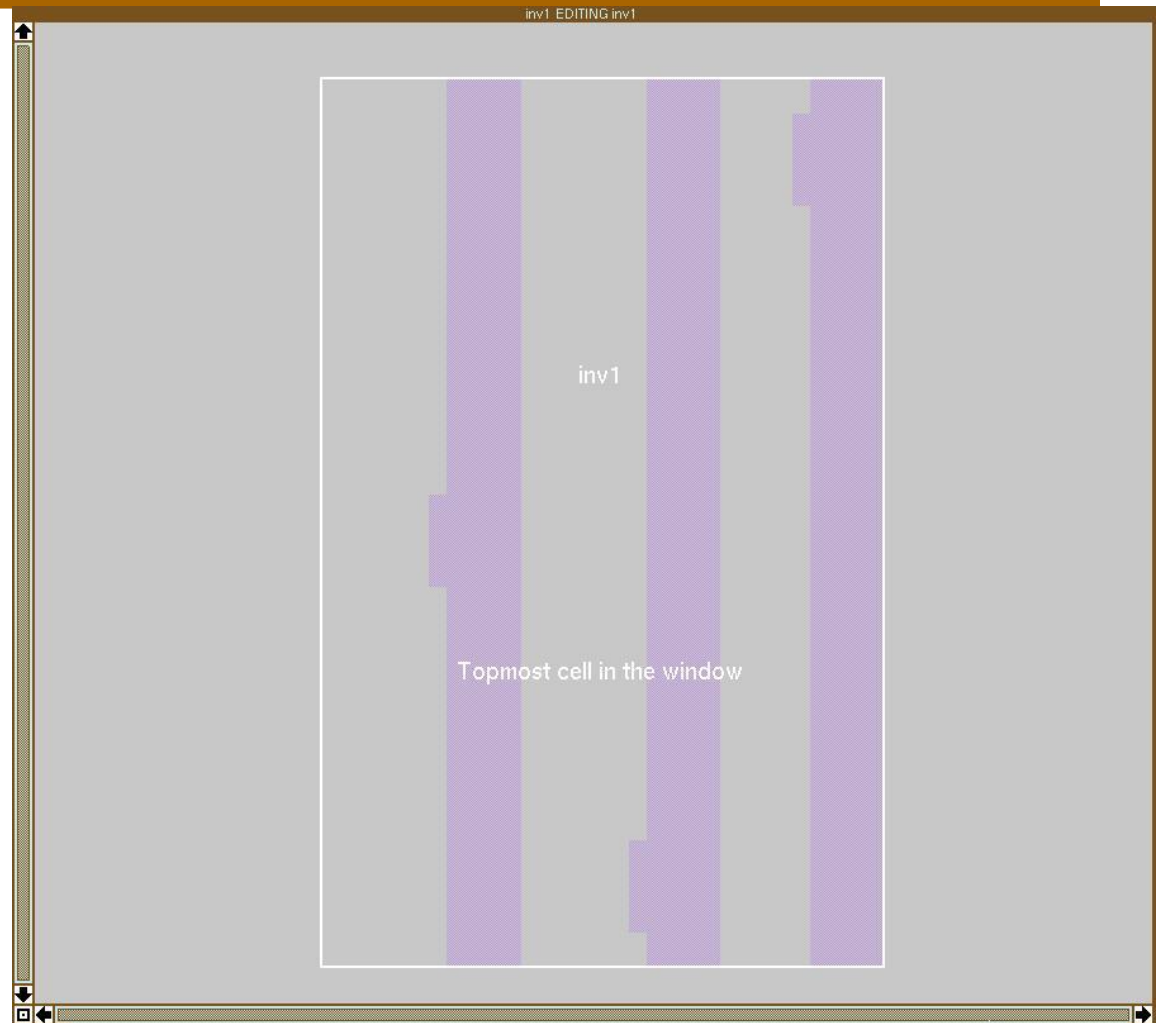
metal1

- First level of interconnect



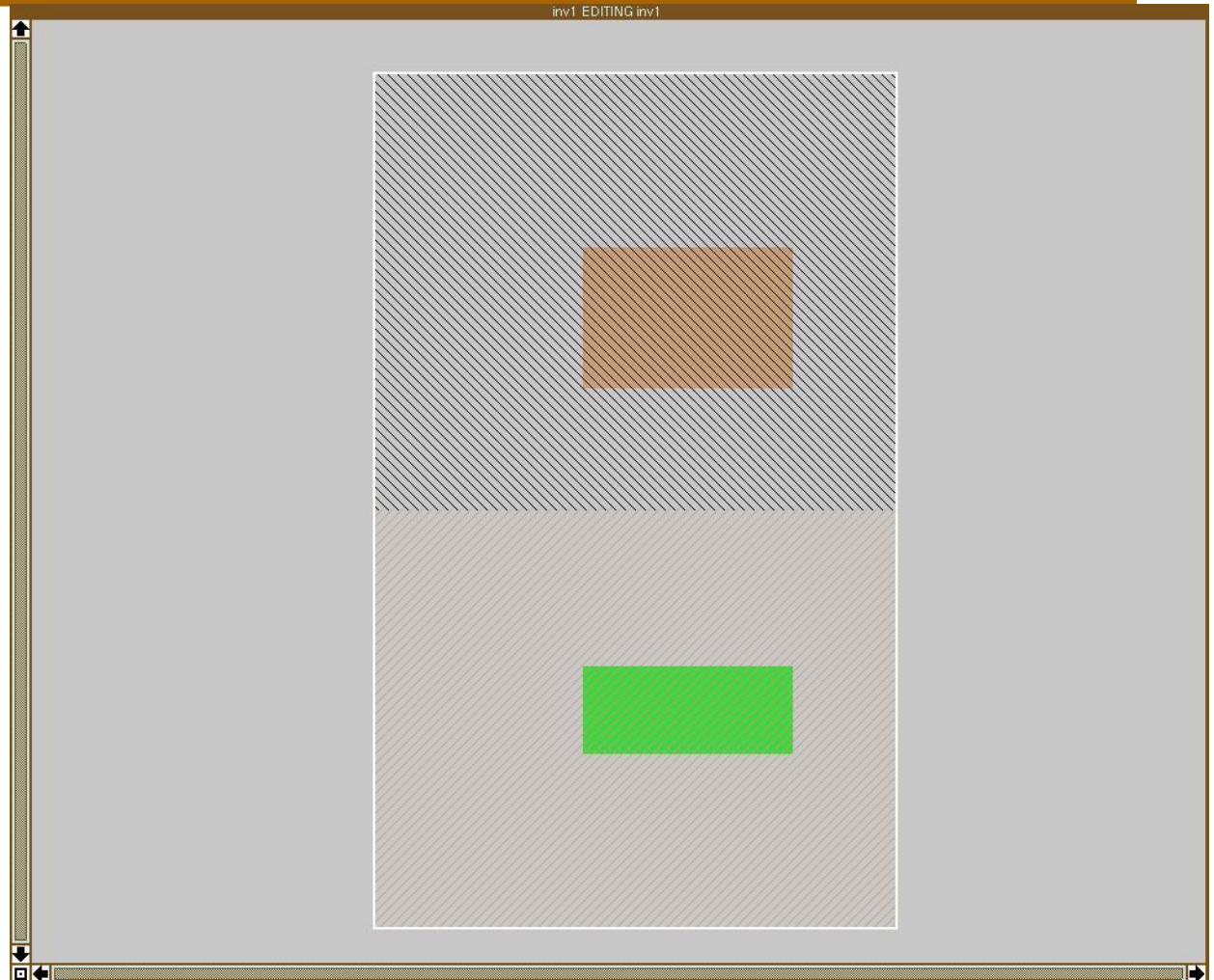
metal2

- Second layer of interconnect



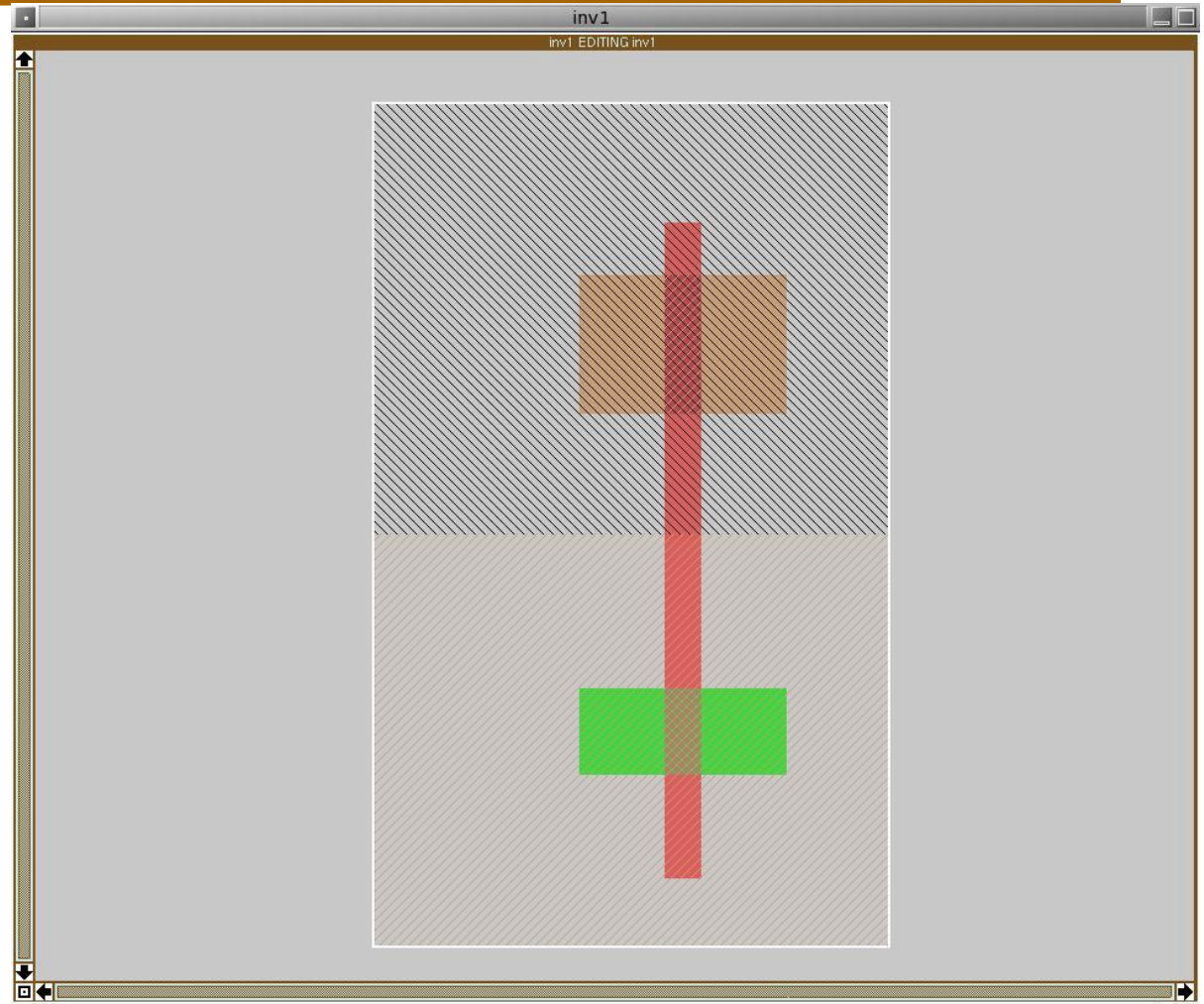
Building an Inverter: Starting with Well and Diffusion

- Place N-type and P-type diffusions
 - Convention is to place PMOS on top and NMOS on bottom



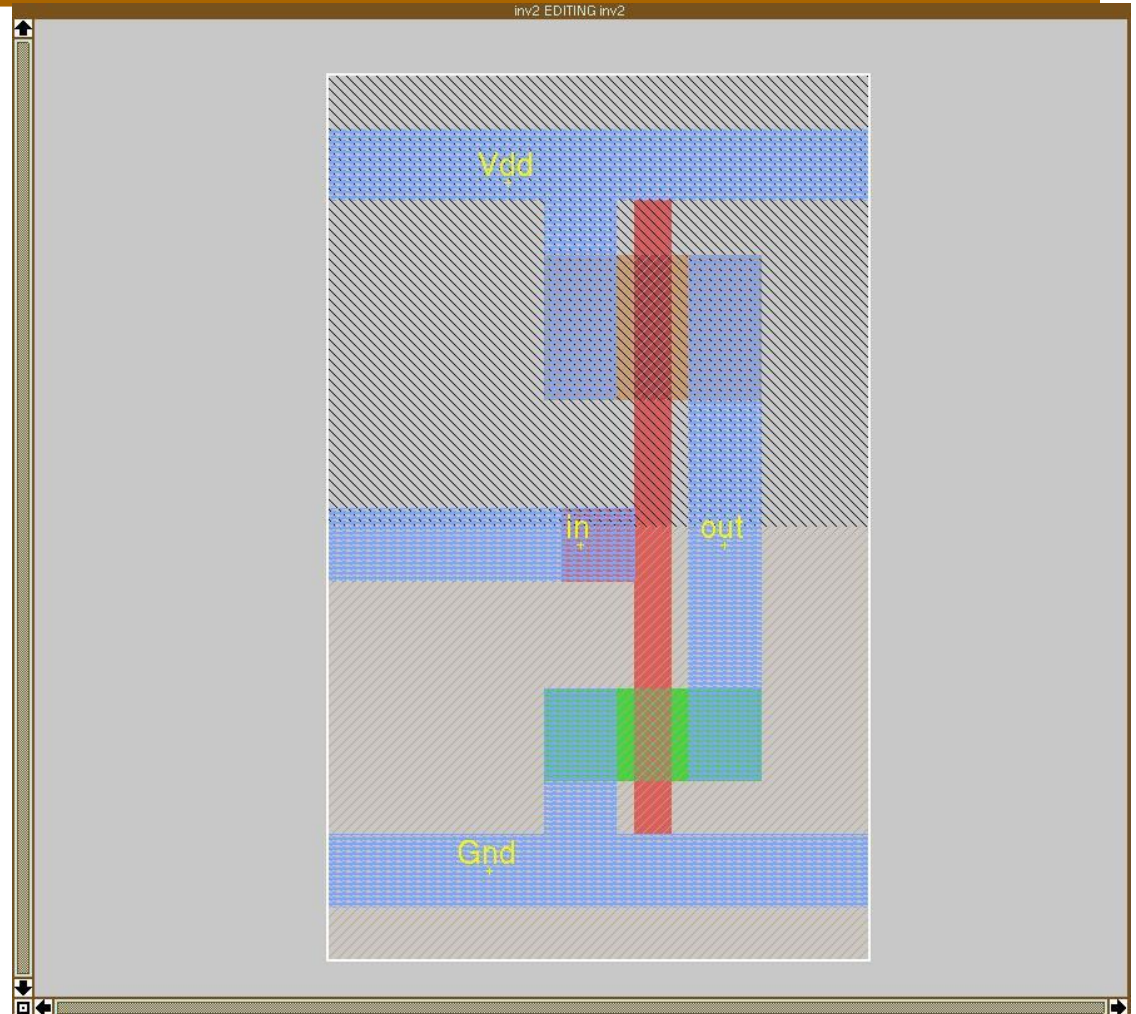
Transistors

- poly crossing diffusion produces a transistor!
- Common gate here
- PMOS shown on top
- NMOS shown on bottom



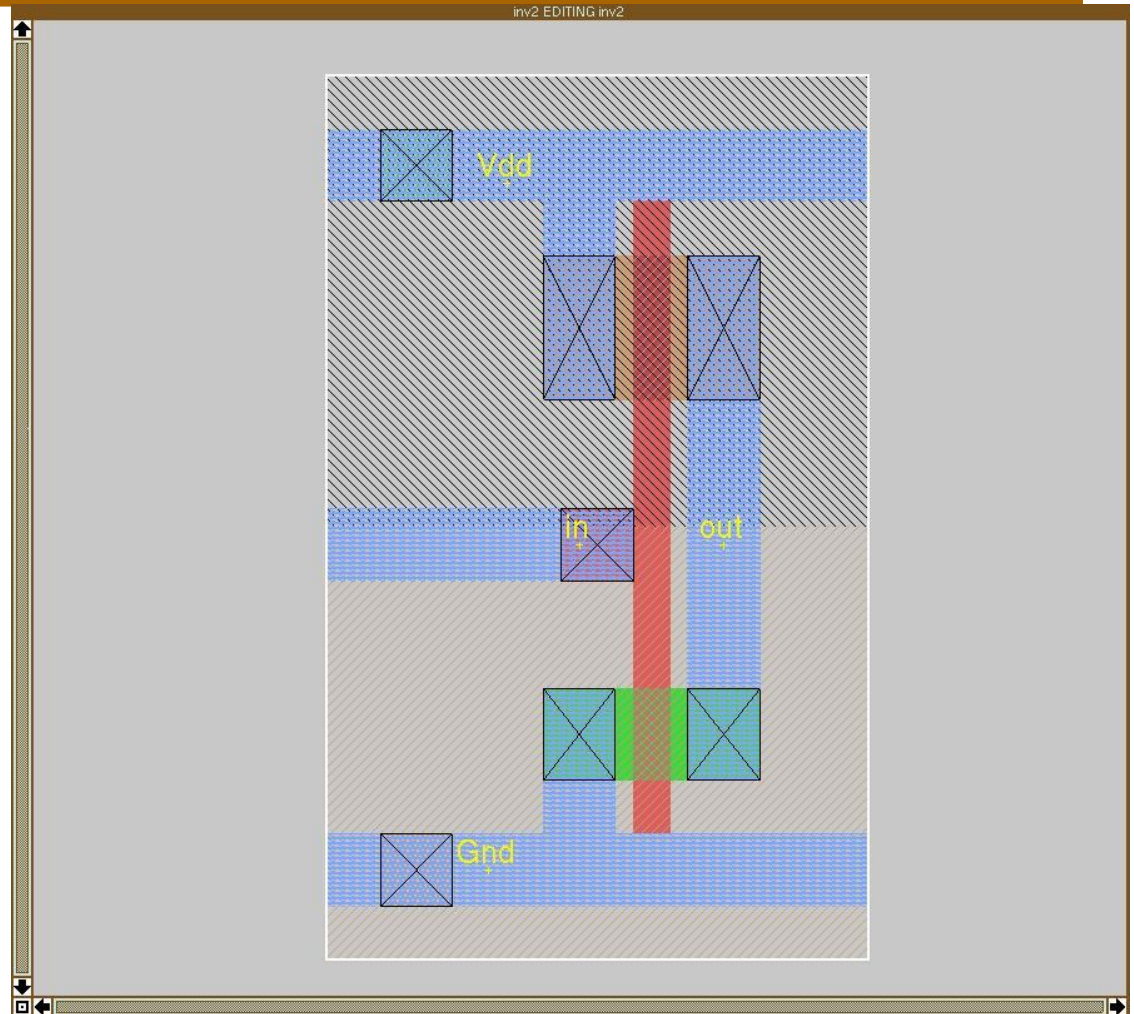
metal1

- metal1 laid down but not yet connected
- Use metal for V_{dd} and G_{nd}
- Labels added
 - Extremely useful for testing
 - Documents design
 - Use “point” labels, not large area ones
 - Never use *global* labels that end in an “!”



metal1 contacts

- Connections now made between metal1 and:
 - pdiff
 - ndiff
 - poly
 - nwell
 - pwell
- Each via/contact is a different layer in magic



metal2

- Use metal2 for longer distance routing
- Routes over the “top” of other circuits shown
- metal2 contacts connect metal1 and metal2 only

